

SST5019 P-CHANNEL JFET



Linear Systems replaces discontinued Siliconix SST5019 The SST5019 is a single P-Channel JFET switch

This p-channel analog switch is designed to provide low on-resistance and fast switching.

The SOT-23 package provides ease of manufacturing, and a lower cost assembly option.

(See Packaging Information).

SST5019 Benefits:

- Low Insertion Loss
- No offset or error voltage generated by closed switch
- Purely resistive

SST5019 Applications:

- **Analog Switches**
- Commutators
- Choppers

FEATURES					
DIRECT REPLACEMENT FOR SILICONIX SST5019					
ZERO OFFSET VOLTAGE					
LOW ON RESISTANCE $r_{DS(on)} \le 150\Omega$					
ABSOLUTE MAXIMUM RATINGS					
@ 25°C (unless otherwise noted)					
Maximum Temperatures					
Storage Temperature	-55°C to +200°C				
Operating Junction Temperature	-55°C to +200°C				
Maximum Power Dissipation					
Continuous Power Dissipation	500mW				
MAXIMUM CURRENT					
Gate Current (Note 1)	I _G = -50mA				
MAXIMUM VOLTAGES					
Gate to Drain Voltage	V _{GDS} = 30V				
Gate to Source Voltage	$V_{GSS} = 30V$				

SST5019 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
BV_{GSS}	Gate to Source Breakdown Voltage	30				$I_G = 1\mu A$, $V_{DS} = 0V$
$V_{GS(off)}$	Gate to Source Cutoff Voltage			5	V	$V_{DS} = -15V$, $I_{D} = -1\mu A$
$V_{DS(on)}$	Drain to Source On Voltage			-0.5		$V_{GS} = 0V$, $I_D = -3mA$
I _{DSS}	Drain to Source Saturation Current (Note 2)	-5			mA	$V_{DS} = -20V, V_{GS} = 0V$
I _{GSS}	Gate Reverse Current			2	nA	$V_{GS} = 15V, \ V_{DS} = 0V$
I _{D(off)}	Drain Cutoff Current			-10		$V_{DS} = -15V, V_{GS} = 12V$
	' 4 0 7			1 0	μA	V _{DS} = -15V, V _{GS} = 7V
I _{DGO}	D <mark>ra</mark> in Re <mark>v</mark> erse Current			-2	nA	V _{DG} = -15V, I _S = 0A
r _{DS(on)}	Drain to Source On Resistance			1 <mark>50</mark>	Ω	$I_{D} = -1 \text{mA}, V_{GS} = 0 \text{V}$

SST5019 DYNAMIC ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
r _{DS(on)}	Drain to Source On Resistance			150	Ω	$I_D = 0A$, $V_{GS} = 0V$, $f = 1kHz$
C_{iss}	Input Capacitance			45	pF	$V_{DS} = -15V$, $V_{GS} = 0V$, $f = 1MHz$
C_{rss}	Reverse Transfer Capacitance			10		$V_{DS} = 0V, V_{GS} = 7V, f = 1MHz$

SST5019 SWITCHING CHARACTERISTICS @ 25°C (unless otherwise noted)

	SYMBOL	CHARACTERISTIC		UNITS	CONDITIONS	
Ī	t _{d(on)}	Turn On Time	15	ns	ns	$V_{GS}(L) = 7V$
ſ	t _r	Turn On Rise Time	75			$V_{GS}(H) = 0V$
Ī	t _{d(off)}	Turn Off Time	25			See Switching Circuit
Į	t _f	Turn Off Fall Time	100		· ·	

Note 1 - Absolute maximum ratings are limiting values above which SST5019 serviceability may be impaired.

SST5019 SWITCHING CIRCUIT PARAMETERS

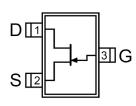
V_{DD}	-6V
V_{GG}	8V
R_L	1.8kΩ
R_{G}	390Ω
I _{D(on)}	-3mA

Micross Components Europe

Available Packages:

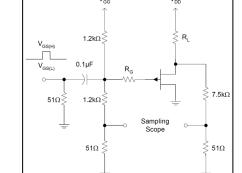
SST5019 in SOT-23 SST5019 in bare die.

Please contact Micross for full package and die dimensions



SOT-23 (Top View)

SWITCHING TEST CIRCUIT





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Note 2 – Pulse test: PW≤ 300 us. Duty Cycle ≤ 3%